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BLX39

NPN SILICON RF POWER TRANSISTOR

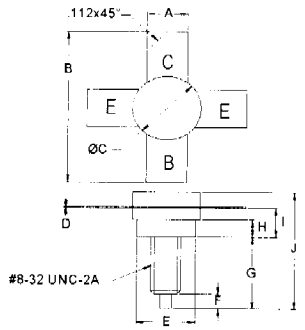
DESCRIPTION:

BLX39 is Designed for broadband amplifier operations up to 175 MHz.

FEATURES:

- P_G = 7.6 dB min. at 40 W/175 MHz
- Emitter Resistors Ballasted
- ***Omnigold***™ Metalization System

PACKAGE STYLE .380 STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

MAXIMUM RATINGS

I_C	5.0 A
V_{CB}	65 V
V_{CE}	35 V
P_{DISS}	60 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.9 °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 50 mA	35			V
BV_{CES}	I_C = 200 mA	65			V
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CES}	V_E = 28 V			5	mA
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	10		100	---
C_{ob}	V_{CB} = 28 V f = 1.0 MHz			65	pF
P_G	V_{CE} = 28 V P_{IN} = 7.0 W f = 175 MHz	7.6			dB
η_C		60			%